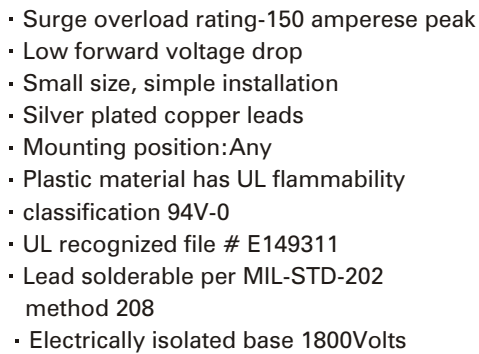


## SINGLE-PHASE SILICON BRIDGE



Dimensions in inches and (millimeters)

		PB605	PB61	PB62	PB64	PB66	PB68	PB610	UNITS
		KBPC6005	KBPC601	KBPC602	KBPC604	KBPC606	KBPC608	KBPC610	
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Bridge Input Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	60	100	200	400	600	800	1000	V
Maximum Average Forward Output Current @ $T_A=50^{\circ}C^*$ @ $T_A=50^{\circ}C^{**}$	$V_{(AV)}$	8.0 6.0							A A
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load	$I_{FSM}$	150							A
Maximum DC Forward Voltage drop per element at 3.0A DC	$V_F$	1.1							V
Maximum DC Reverse Current at rated DC Blocking Voltage Per Element @ $T_A=100^{\circ}C$	$I_R$	10 1							$\mu A$ mA
$I^2t$ Rating for fusing( $t<8.3ms$ )	$I^2t$	64							A <sup>2</sup> S
Typical Thermal Resistance	$R_{\theta JC}$	8							$^{\circ}C/W$
Operating Temperature Range	$T_J$	-55 to +125							$^{\circ}C$
Storage Temperature Range	$T_{STG}$	-55 to +150							$^{\circ}C$

# PB6 SERIES KBPC6 SERIES

SINGLE-PHASE SILICON BRIDGE

**CHENG-YI  
ELECTRONIC**

## RATING AND CHARACTERISTICS CURVES KBPC6 SERIES

Fig.1 - DERATING CURVE FOR  
OUTPUT RECTIFIED CURRENT

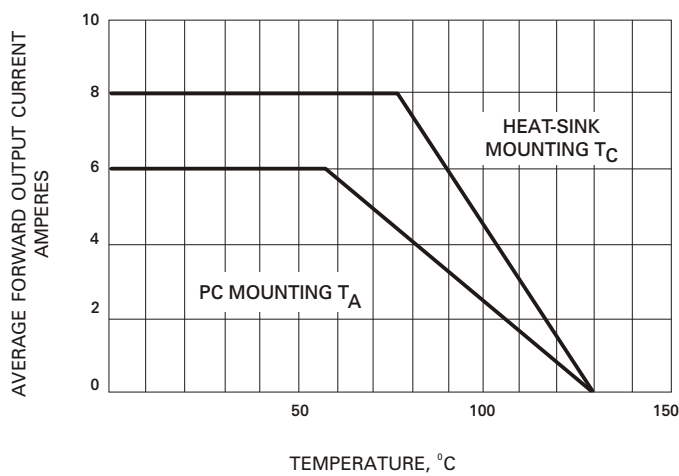


Fig.2 - TYPICAL REVERSE  
CHARACTERISTICS

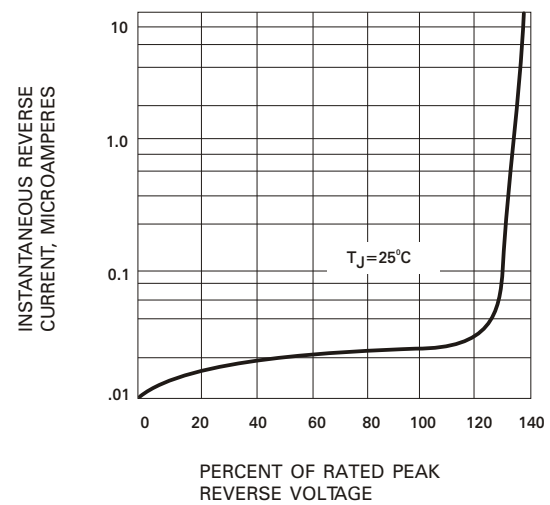


Fig.3 - MAXIMUM FORWARD SURGE CURRENT

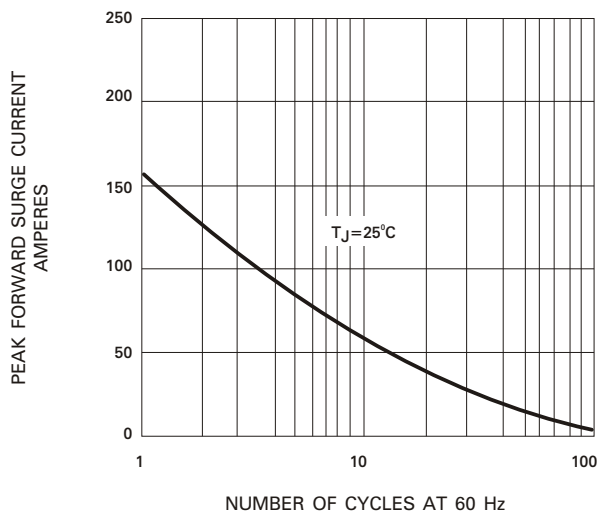


Fig.4 - TYPICAL INSTANTANEOUS FORWARD  
CHARACTERISTICS

